

1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- Isolated package

3. Applications

- General purpose motor control
- General purpose switching

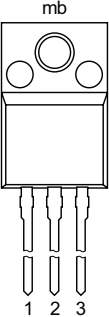
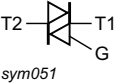
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V _{DRM}	repetitive peak off-state voltage		600				V
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 73 °C; Fig. 1 ; Fig. 2 ; Fig. 3	8				A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; Fig. 4 ; Fig. 5	65				A
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7		-	5	25	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7		-	8	25	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		-	11	25	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _i = 25 °C; Fig. 7		-	30	70	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT137X-600F	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Marking

Table 4. Marking codes

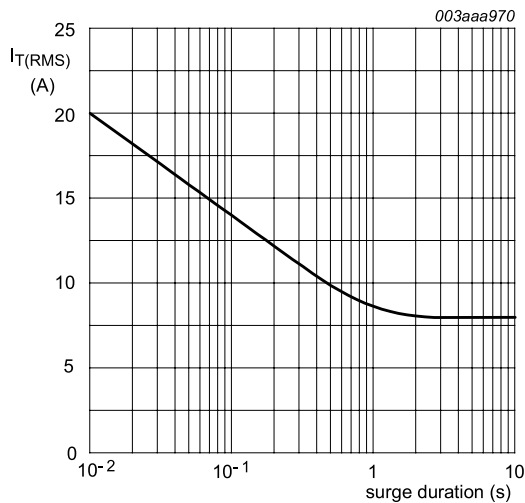
Type number	Marking codes
BT137X-600F	BT137X-600F

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_h \leq 73\text{ }^{\circ}\text{C}$; Fig 1 ; Fig 2 ; Fig 3	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig 4 ; Fig 5	65	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$	71	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	21	A^2s
dl_{T}/dt	rate of rise of on-state current	$I_G = 50\text{ mA}$; T2+ G+	50	$\text{A}/\mu\text{s}$
		$I_G = 50\text{ mA}$; T2+ G-	50	$\text{A}/\mu\text{s}$
		$I_G = 50\text{ mA}$; T2- G-	50	$\text{A}/\mu\text{s}$
		$I_G = 140\text{ mA}$; T2- G+	140	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	$^{\circ}\text{C}$
T_{j}	junction temperature		125	$^{\circ}\text{C}$



$f = 50\text{ Hz}$; $T_h = 73\text{ }^{\circ}\text{C}$

Fig. 1. RMS on-state current as a function of surge duration; maximum values

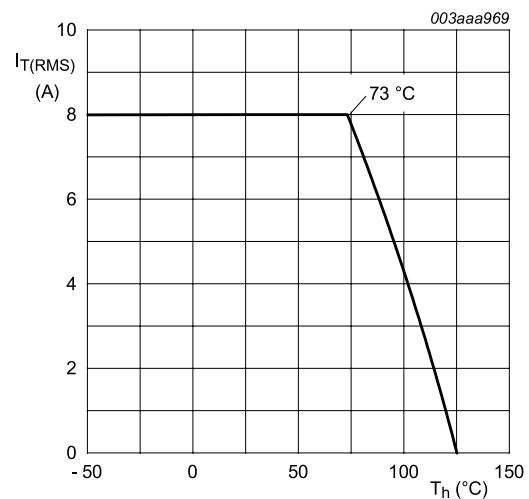


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

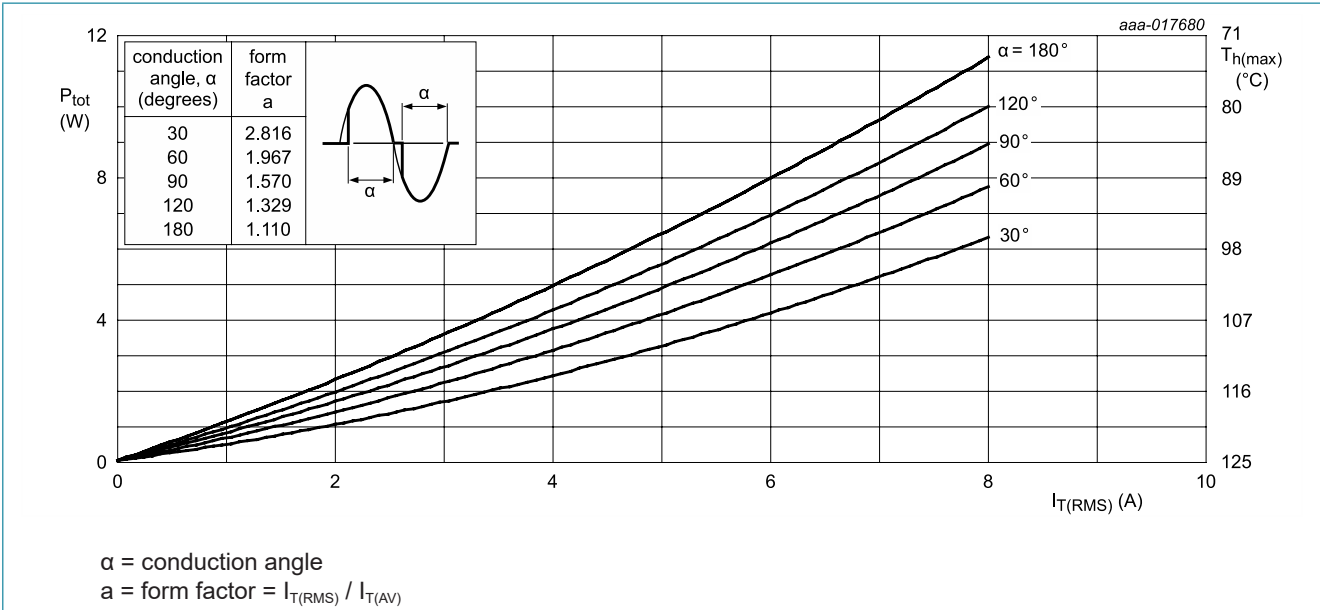


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

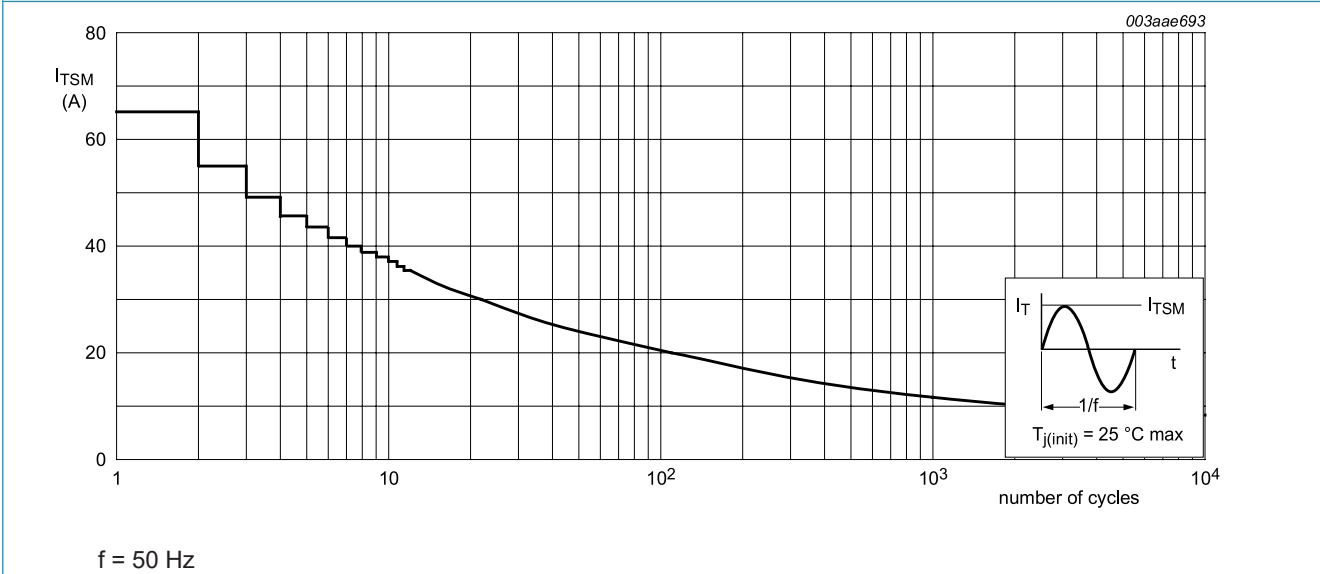
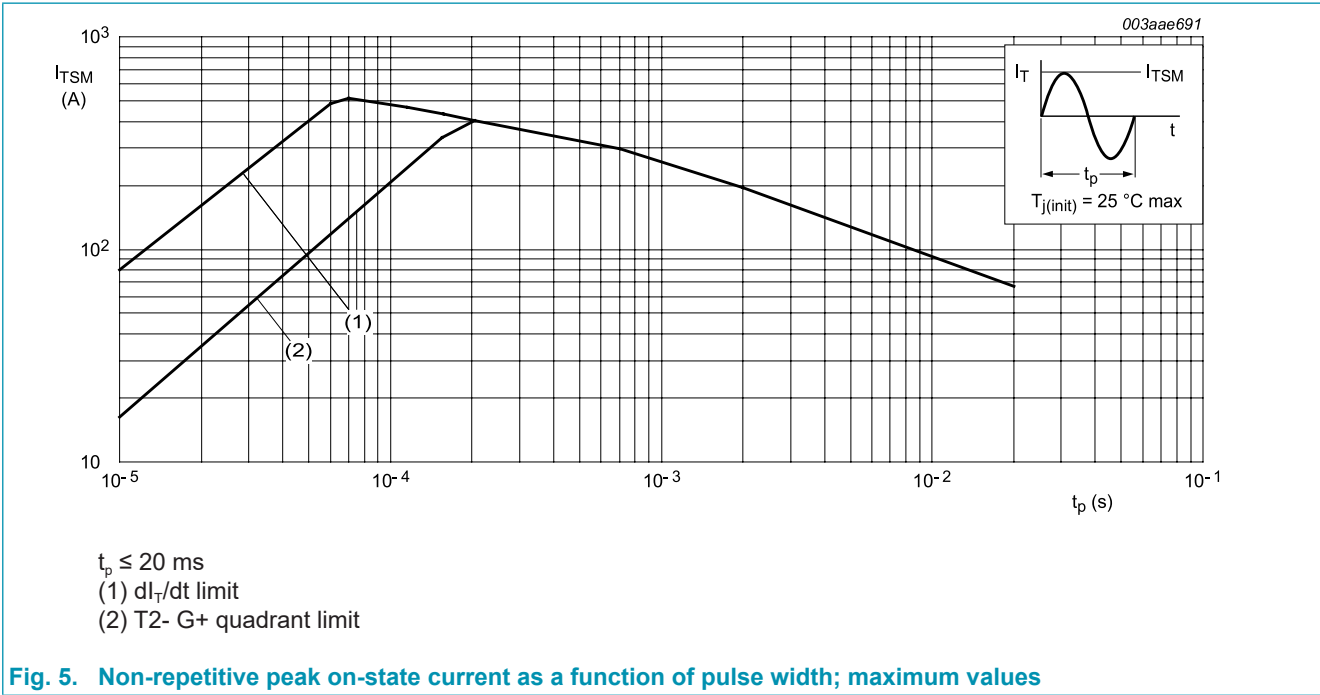


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle; with heatsink compound; Fig 6	-	-	4.5	K/W
		full or half cycle; without heatsink compound; Fig 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

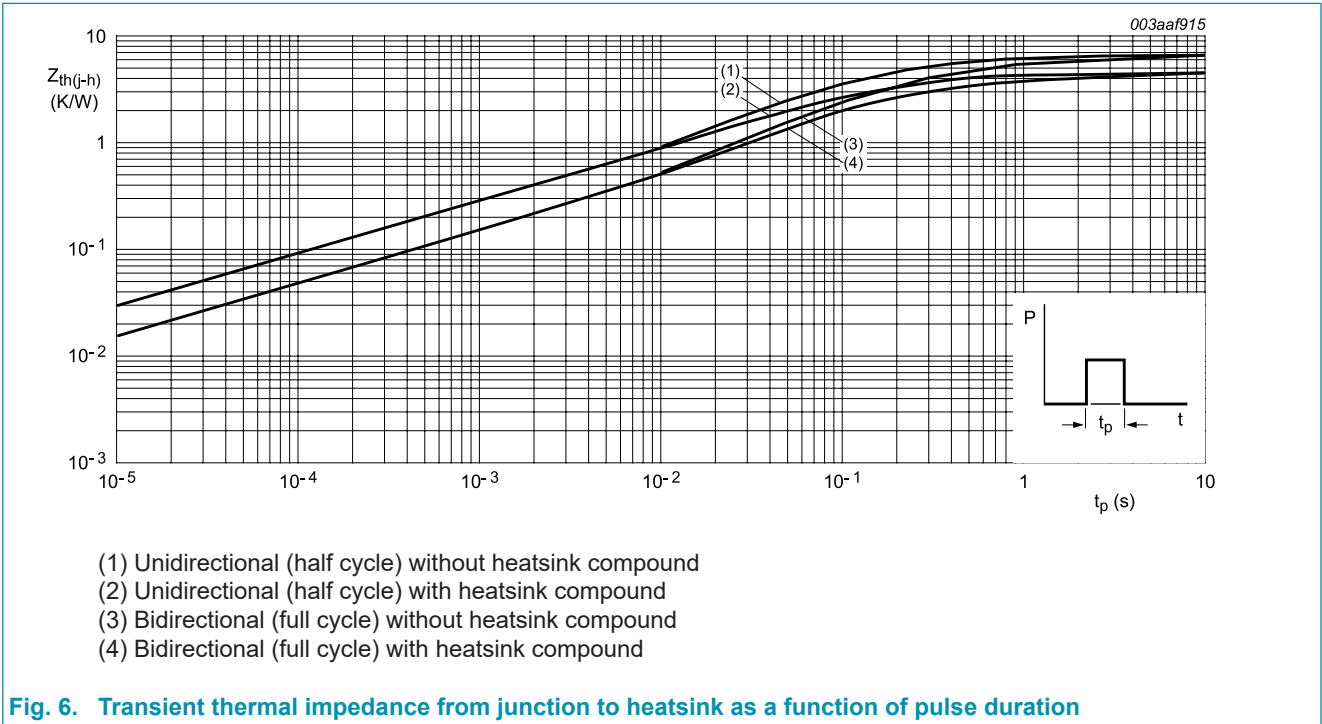


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

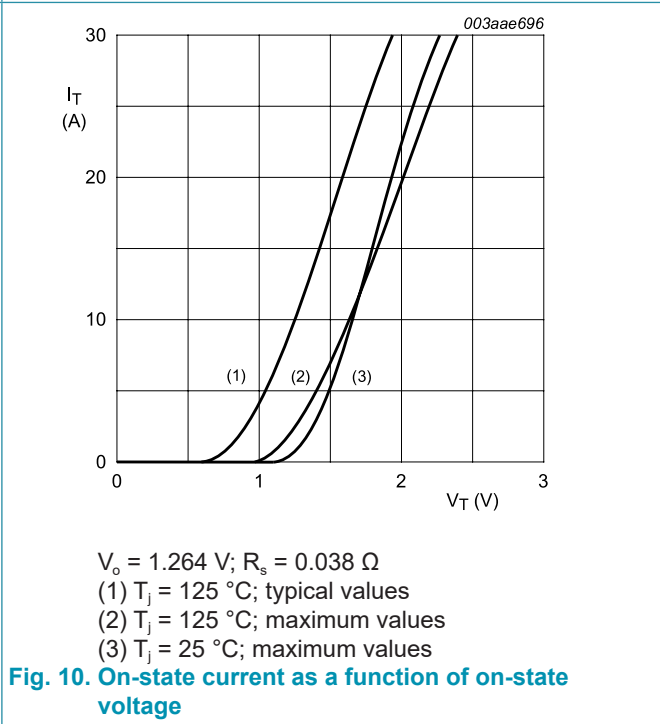
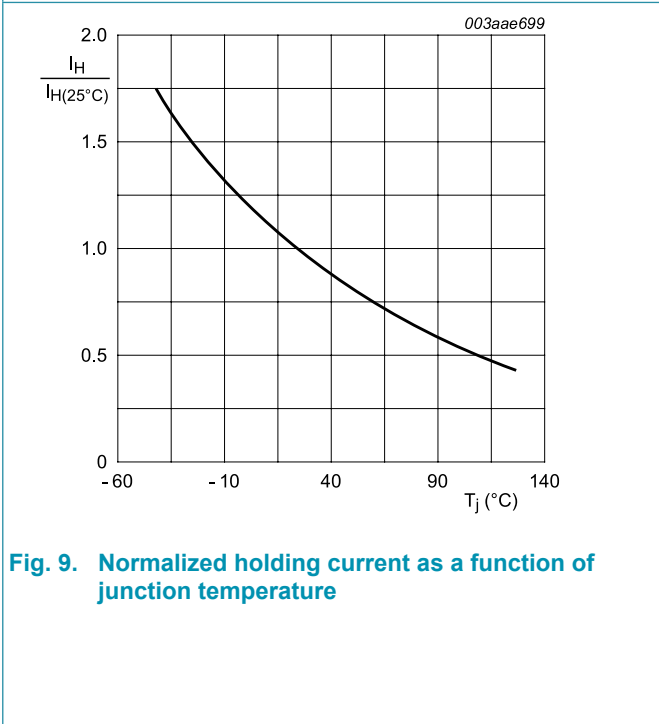
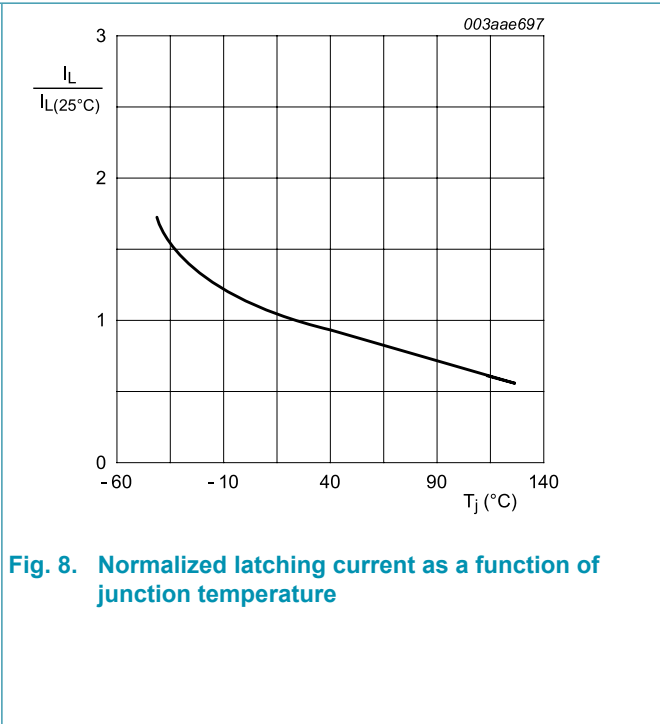
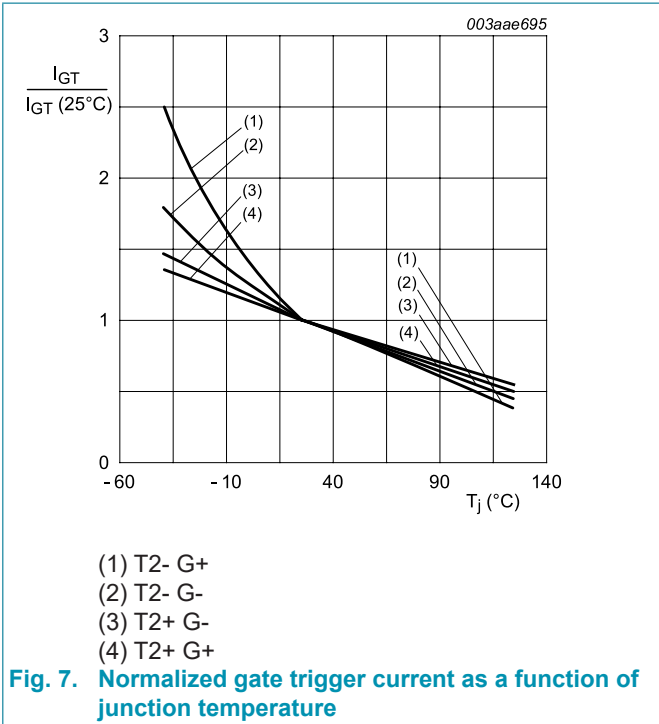
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; T _h = 25 °C	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	5	25	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	8	25	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	11	25	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	30	70	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	7	30	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	16	45	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	5	30	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	7	45	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	5	20	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11		-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 125\text{ }^\circ\text{C}$; Fig. 11		0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		50	250	-	V/ μs
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_J = 95\text{ }^\circ\text{C}$; $dI_{com}/dt = 3.6\text{ A/ms}$; $I_T = 8\text{ A}$		-	20	-	V/ μs
t_{gt}	gate-controlled turn-on time	$V_D = 600\text{ V}$; $I_{TM} = 12\text{ A}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$		-	2	-	μs



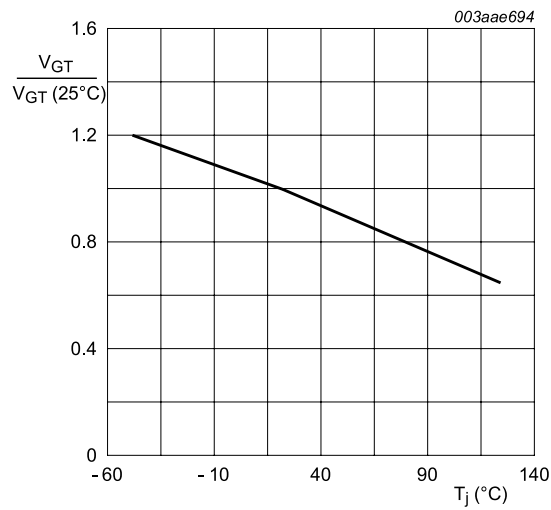


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" SOT186A



UNIT	A	A ₁	b	b ₁	b ₂	c	D	D ₁	E	e	e ₁	j ⁽²⁾	k ⁽²⁾	L	L ₁	L ₂ ⁽¹⁾ max.	P	Q	q	W	T ⁽³⁾
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3	2.54	5.08	2.7	0.6	14.4	3.30	3	3.2	2.6	3.0	0.4	2.5
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7			1.7	0.4	13.5	2.79		3.0	2.3	2.6		

- Notes
- 1. Terminal dimensions within this zone are uncontrolled
 - 2. Dot lines area designs may vary
 - 3. Eject pin mark is for reference only

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3 LEADS TO220F				2013-11-14

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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14. Contents

1. General description.....	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Marking.....	2
8. Limiting values	3
9. Thermal characteristics	6
10. Isolation Characteristics.....	6
11. Characteristics.....	7
12. Package outline	10
13. Legal information	11
14. Contents	13

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